Takashi Suemasu

List of Publications by Year in Descending Order

418 papers	6,762 citations	39 h-index	58 g-index
455 ext. papers	7,797 ext. citations	2.3 avg, IF	6.17 L-index

#	Paper	IF	Citations
418	Growth conditions for high-photoresponsivity randomly oriented polycrystalline BaSi2 films by radio-frequency sputtering: Comparison with BaSi2 epitaxial films. *Applied Physics Express*, **2022**, 15, 025502	2.4	2
417	Three-Dimensionally Orientation-Controlled Ge Rods on an Insulator Formed by Low-Temperature Ni-Induced Lateral Crystallization. *Crystal Growth and Design*, **2022**, 22, 1123-1129	3.5	
416	High-temperature post-annealing effect on the surface morphology and photoresponse and electrical properties of B-doped BaSi2 films grown by molecular beam epitaxy under various Ba-to-Si deposition rate ratios. *Journal of Crystal Growth*, **2022**, 578, 126429	1.6	1
415	Molecular beam epitaxial growth and magneto-transport properties of Mn4□N films on SrTiO3(001) and MgO(001) substrates. *Journal of Crystal Growth*, **2022**, 582, 126525	1.6	2
414	ZnGeO Passivating Interlayers for BaSi Thin-Film Solar Cells.. *ACS Applied Materials & Interfaces* , **2022**,	9.5	1
413	Record-High Hole Mobility Germanium on Flexible Plastic with Controlled Interfacial Reaction. *ACS Applied Electronic Materials*, **2022**, 4, 269-275	4	1
412	High electron mobility in randomly oriented polycrystalline BaSi2 films formed through radio-frequency sputtering. *AIP Advances*, **2022**, 12, 045120	1.5	1
411	Silicon meets group-II metals in energy and electronic applications□How to handle reactive sources for high-quality films and bulk crystals. *Journal of Applied Physics*, **2022**, 131, 191101	2.5	0
410	Hydrogen impurities in p-type semiconductors, GeS and GeTe. *Journal of Applied Physics*, **2021**, 130, 195704	2.5	0
409	Sn Concentration Effects on Polycrystalline GeSn Thin Film Transistors. *IEEE Electron Device Letters*, **2021**, 42, 1735-1738	4.4	0
408	Low thermal conductivity of complex thermoelectric barium silicide film epitaxially grown on Si. *Applied Physics Letters*, **2021**, 119, 141603	3.4	3
407	Effects of Ba-to-Si deposition rate ratios on the electrical and photoresponse properties of arsenic-doped n-type BaSi2 films. *Thin Solid Films*, **2021**, 738, 138969	2.2	0
406	Strain effects on polycrystalline germanium thin films. *Scientific Reports*, **2021**, 11, 8333	4.9	8
405	Comparison of C doping technique between SiC and C targets for high-photoresponsivity BaSi2 films by radio-frequency sputtering. *Japanese Journal of Applied Physics*, **2021**, 60, 058001	1.4	4
404	Mechanisms of carrier lifetime enhancement and conductivity-type switching on hydrogen-incorporated arsenic-doped BaSi2. *Thin Solid Films*, **2021**, 724, 138629	2.2	5
403	Solar cell operation of sputter-deposited n-BaSi2/p-Si heterojunction diodes and characterization of defects by deep-level transient spectroscopy. *Applied Physics Express*, **2021**, 14, 051010	2.4	2
402	Grain size dependent photoresponsivity in GaAs films formed on glass with Ge seed layers. *Scientific Reports*, **2021**, 11, 10159	4.9	1

401	Epitaxial growth of BaSi2 thin films by co-sputtering of Ba and Si for solar cell applications. *Applied Physics Express*, **2021**, 14, 065501	2.4	3
400	Solid-phase crystallization of gallium arsenide thin films on insulators. *Materials Science in Semiconductor Processing*, **2021**, 124, 105623	4.3	1
399	Formation of high-photoresponsivity BaSi2 films on glass substrate by radio-frequency sputtering for solar cell applications. *Journal Physics D: Applied Physics*, **2021**, 54, 135106	3	6
398	Thickness-dependent thermoelectric properties of Si1−xGex films formed by Al-induced layer exchange. *Journal of Applied Physics*, **2021**, 129, 015303	2.5	4
397	Current-Driven Domain Wall Dynamics in Ferrimagnetic Nickel-Doped MnN Films: Very Large Domain Wall Velocities and Reversal of Motion Direction across the Magnetic Compensation Point. *Nano Letters*, **2021**, 21, 2580-2587	11.5	18
396	Present Status of Rare-earth Free Ferrimagnet Mn4N and Future Prospects of Mn4N-based Compensated Ferrimagnets. *Journal of the Physical Society of Japan*, **2021**, 90, 081010	1.5	7
395	Solar cells based on n+-AZO/p-BaSi2 heterojunction: Advanced opto-electrical modelling and experimental demonstration. *Solar Energy Materials and Solar Cells*, **2021**, 230, 111181	6.4	4
394	High thermoelectric power factors in polycrystalline germanium thin films. *Applied Physics Letters*, **2021**, 119, 132101	3.4	1
393	Fabrication of heterojunction crystalline Si solar cells with BaSi2 thin films prepared by a two-step evaporation method. *Japanese Journal of Applied Physics*, **2021**, 60, 105503	1.4	6
392	Synthesis and magnetic properties of tetragonally ordered Fe2Ni2N alloy using topotactic nitriding reaction. *Journal of Alloys and Compounds*, **2021**, 885, 161122	5.7	2
391	Composition dependent properties of p- and n-type polycrystalline group-IV alloy thin films. *Journal of Alloys and Compounds*, **2021**, 887, 161306	5.7	3
390	Effect of post-annealing on the significant photoresponsivity enhancement of BaSi2 epitaxial films on Si(111). *Applied Physics Express*, **2021**, 14, 021003	2.4	2
389	Zn-induced layer exchange of p- and n-type nanocrystalline SiGe layers for flexible thermoelectrics. *Applied Physics Letters*, **2020**, 116, 182105	3.4	8
388	Metal-induced layer exchange of group IV materials. *Journal Physics D: Applied Physics*, **2020**, 53, 373002	3	22
387	Drastic enhancement of photoresponsivity in C-doped BaSi2 films formed by radio-frequency sputtering. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA06	1.4	4
386	Effects of sputtering pressure and temperature of ITO electrodes on the performance of p-BaSi2/n-Si heterojunction solar cells. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA07	1.4	
385	Significant enhancement of photoresponsivity in As-doped n-BaSi2epitaxial films by atomic hydrogen passivation. *Applied Physics Express*, **2020**, 13, 051001	2.4	5
384	Effects of boron and hydrogen doping on the enhancement of photoresponsivity and photoluminescence of BaSi2 epitaxial films. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA08	1.4	2

383	Fabrication of As-doped n-type BaSi2 epitaxial films grown by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA01	1.4	6
382	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi2 films and performance improvement of boron-doped p-BaSi2/n-Si heterojunction solar cells. *Journal of Applied Physics*, **2020**, 127, 233104	2.5	8
381	Hydrogen states in hydrogen-passivated semiconducting barium disilicide measured via muon spin rotation. *Japanese Journal of Applied Physics*, **2020**, 59, 071004	1.4	7
380	Strong correlation between uniaxial magnetic anisotropic constant and in-plane tensile strain in Mn4N epitaxial films. *AIP Advances*, **2020**, 10, 025117	1.5	15
379	Manipulation of saturation magnetization and perpendicular magnetic anisotropy in epitaxial CoxMn4−xN films with ferrimagnetic compensation. *Physical Review B*, **2020**, 101,	3.3	11
378	Perpendicular magnetic anisotropy in ferrimagnetic Mn4N films grown on (LaAlO3)0.3(Sr2TaAlO6)0.7(0□0□1) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2020**, 535, 125566	1.6	9
377	Improving photoresponsivity in GaAs film grown on Al-induced-crystallized Ge on an insulator. *AIP Advances*, **2020**, 10, 015153	1.5	3
376	Fabrication of high-photoresponsivity BaSi2films formed on conductive layers by radio-frequency sputtering. *Applied Physics Express*, **2020**, 13, 075506	2.4	1
375	Point defects in BaSi2 thin films for photovoltaic applications studied by positron annihilation spectroscopy. *Journal of Applied Physics*, **2020**, 127, 085304	2.5	6
374	Improved thermoelectric performance of flexible p-type SiGe films by B-doped Al-induced layer exchange. *Journal Physics D: Applied Physics*, **2020**, 53, 075105	3	6
373	Magnetic reversal in rare-earth free Mn4−xNixN epitaxial films below and above Ni composition needed for magnetic compensation around room temperature. *Journal of Applied Physics*, **2020**, 127, 043903	2.5	14
372	Impact of the carbon membrane inserted below Ni in the layer exchange of multilayer graphene. *CrystEngComm*, **2020**, 22, 3106-3109	3.3	1
371	Underlayer Selection to Improve the Performance of Polycrystalline Ge Thin Film Transistors. *ECS Transactions*, **2020**, 98, 423-427	1	2
370	Effects of molecular beam epitaxy growth conditions on grain size and lattice strain in a-axis-oriented BaSi2 films. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA09	1.4	3
369	Impact of radio-frequency power on the photoresponsivity enhancement of BaSi2 films formed by sputtering. *Applied Physics Express*, **2020**, 13, 085511	2.4	6
368	Four-step heating process for solid-phase crystallization of Ge leading to high carrier mobility. *Applied Physics Express*, **2020**, 13, 101005	2.4	2
367	Magnetic compensation at two different composition ratios in rare-earth-free Mn4−xCoxN ferrimagnetic films. *Physical Review Materials*, **2020**, 4,	3.2	11
366	Modeling the effects of defect parameters on the performance of a p-BaSi2/n-Si heterojunction solar cell. *Solar Energy Materials and Solar Cells*, **2020**, 205, 110244	6.4	3

365	Formation of poly-crystalline BaSi2 thin films by pulsed laser deposition for solar cell applications. *Materials Letters*, **2020**, 260, 126936	3.3	1
364	Growth and fluorination of CaSi2 thin film. *Japanese Journal of Applied Physics*, **2020**, 59, SFFC02	1.4	2
363	Influence of Ba-to-Si deposition rate ratios on the electrical and optical properties of B-doped BaSi2 epitaxial films. *Japanese Journal of Applied Physics*, **2020**, 59, SFFA04	1.4	6
362	Fe-induced layer exchange of multilayer graphene for rechargeable battery anodes. *Applied Physics Express*, **2020**, 13, 025501	2.4	4
361	Thin-film thermoelectric generator based on polycrystalline SiGe formed by Ag-induced layer exchange. *Applied Physics Letters*, **2020**, 117, 162103	3.4	3
360	Multilayer Graphene Battery Anodes on Plastic Sheets for Flexible Electronics. *ACS Applied Energy Materials*, **2020**, 3, 8410-8414	6.1	2
359	Influence of grain boundaries on the properties of polycrystalline germanium. *Journal of Applied Physics*, **2020**, 128, 075301	2.5	2
358	350 ℃ synthesis of high-quality multilayer graphene on an insulator using Ni-induced layer exchange. *Applied Physics Express*, **2020**, 13, 055502	2.4	6
357	Impact of deposition pressure and two-step growth technique on the photoresponsivity enhancement of polycrystalline BaSi2 films formed by sputtering. *Applied Physics Express*, **2019**, 12, 021004	2.4	9
356	Stability of cross-shaped electron beam in a vacuum magnetic sensor with a p-Si field emitter tip. *Vacuum*, **2019**, 168, 108858	3.7	2
355	Magnetic and magneto-transport properties of Mn4N thin films by Ni substitution and their possibility of magnetic compensation. *Journal of Applied Physics*, **2019**, 125, 213902	2.5	19
354	Investigation of native defects in BaSi2 epitaxial films by electron paramagnetic resonance. *Applied Physics Express*, **2019**, 12, 061005	2.4	7
353	80 ℃ synthesis of thermoelectric nanocrystalline Ge film on flexible plastic substrate by Zn-induced layer exchange. *Applied Physics Express*, **2019**, 12, 055501	2.4	9
352	Minority carrier lifetime of Ge film epitaxial grown on a large-grain seed layer on glass. *Thin Solid Films*, **2019**, 681, 98-102	2.2	2
351	Solid-phase crystallization of densified amorphous GeSn leading to high hole mobility (540 cm2/V s). *Applied Physics Letters*, **2019**, 114, 112110	3.4	10
350	Operation of BaSi2 homojunction solar cells on p+-Si(111) substrates and the effect of structure parameters on their performance. *Applied Physics Express*, **2019**, 12, 041005	2.4	32
349	High-Electrical-Conductivity Multilayer Graphene Formed by Layer Exchange with Controlled Thickness and Interlayer. *Scientific Reports*, **2019**, 9, 4068	4.9	48
348	Study of a reversible resistive switching mechanism in bismuth titanate deposited by electron cyclotron resonance sputtering. *Japanese Journal of Applied Physics*, **2019**, 58, 045502	1.4	

347	High photoresponsivity in a GaAs film synthesized on glass using a pseudo-single-crystal Ge seed layer. *Applied Physics Letters*, **2019**, 114, 142103	3.4	7
346	Low-Temperature (400 °C) Synthesis of Multilayer Graphene by Metal-Assisted Sputtering Deposition. *ACS Omega*, **2019**, 4, 6677-6680	3.9	12
345	Sb-doped crystallization of densified precursor for n-type polycrystalline Ge on an insulator with high carrier mobility. *Applied Physics Letters*, **2019**, 114, 082105	3.4	14
344	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi2 films by Raman spectroscopy. *Applied Physics Express*, **2019**, 12, 055506	2.4	24
343	Impact of Amorphous-C/Ni Multilayers on Ni-Induced Layer Exchange for Multilayer Graphene on Insulators. *ACS Omega*, **2019**, 4, 14251-14254	3.9	4
342	Effects of lattice parameter manipulations on electronic and optical properties of BaSi2. *Thin Solid Films*, **2019**, 686, 137436	2.2	5
341	Investigation of defect levels in BaSi2 epitaxial films by photoluminescence and the effect of atomic hydrogen passivation. *Journal of Physics Communications*, **2019**, 3, 075005	1.2	6
340	Polycrystalline thin-film transistors fabricated on high-mobility solid-phase-crystallized Ge on glass. *Applied Physics Letters*, **2019**, 114, 212107	3.4	17
339	Large Current Driven Domain Wall Mobility and Gate Tuning of Coercivity in Ferrimagnetic MnN Thin Films. *Nano Letters*, **2019**, 19, 8716-8723	11.5	25
338	Correlation of native defects between epitaxial films and polycrystalline BaSi2 bulks based on photoluminescence spectra. *Applied Physics Express*, **2019**, 12, 111001	2.4	3
337	Marked enhancement of the photoresponsivity and minority-carrier lifetime of BaSi2 passivated with atomic hydrogen. *Physical Review Materials*, **2019**, 3,	3.2	15
336	Fabrication of L10-FeNi films by denitriding FeNiN films. *Journal of the Magnetics Society of Japan*, **2019**, 43, 79-83	0.7	3
335	Nanoscale measurement of giant saturation magnetization in α″-FeN by electron energy-loss magnetic chiral dichroism. *Ultramicroscopy*, **2019**, 203, 37-43	3.1	4
334	High-electron-mobility (370 cm/Vs) polycrystalline Ge on an insulator formed by As-doped solid-phase crystallization. *Scientific Reports*, **2019**, 9, 16558	4.9	12
333	Three-step growth of highly photoresponsive BaSi2 light absorbing layers with uniform Ba to Si atomic ratios. *Journal of Applied Physics*, **2019**, 126, 215301	2.5	13
332	High hole mobility (500 cm2 V−1 s−1) polycrystalline Ge films on GeO2-coated glass and plastic substrates. *Applied Physics Express*, **2019**, 12, 015508	2.4	20
331	Molecular beam epitaxy growth of Mn4−xNi N thin films on MgO(0 0 1) substrates and their magnetic properties. *Journal of Crystal Growth*, **2019**, 507, 163-167	1.6	15
330	Epitaxial growth and magnetic properties of Fe 4−x Mn x N thin films grown on MgO(0 0 1) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2018**, 489, 20-23	1.6	16

329	Impact of Ba to Si deposition rate ratios during molecular beam epitaxy on carrier concentration and spectral response of BaSi2 epitaxial films. *Journal of Applied Physics*, **2018**, 123, 045703	2.5	41
328	Advanced solid-phase crystallization for high-hole mobility (450 cm2V−1s−1) Ge thin film on insulator. *Applied Physics Express*, **2018**, 11, 031302	2.4	18
327	Reduction in interface defect density in p-BaSi2/n-Si heterojunction solar cells by a modified pretreatment of the Si substrate. *Japanese Journal of Applied Physics*, **2018**, 57, 025501	1.4	6
326	Structural characterization and magnetic properties of L10-MnAl films grown on different underlayers by molecular beam epitaxy. *Journal of Crystal Growth*, **2018**, 486, 19-23	1.6	3
325	Decrease in electrical contact resistance of Sb-doped n+-BaSi2layers and spectral response of an Sb-doped n+-BaSi2/undoped BaSi2structure for solar cells. *Japanese Journal of Applied Physics*, **2018**, 57, 031202	1.4	2
324	Transport properties of n- and p-type polycrystalline BaSi2. *Thin Solid Films*, **2018**, 661, 7-15	2.2	14
323	p-BaSi2/n-Si heterojunction solar cells on Si(001) with conversion efficiency approaching 10%: comparison with Si(111). *Applied Physics Express*, **2018**, 11, 062301	2.4	25
322	Detection of local vibrational modes induced by intrinsic defects in undoped BaSi2 light absorber layers using Raman spectroscopy. *Journal of Applied Physics*, **2018**, 124, 025301	2.5	16
321	Fabrication of SrGe thin films on Ge (100), (110), and (111) substrates. *Nanoscale Research Letters*, **2018**, 13, 22	5	1
320	Preferred site occupation of 3d atoms in NixFe4−xN(x=1 and 3) films revealed by x-ray absorption spectroscopy and magnetic circular dichroism. *Physical Review Materials*, **2018**, 2,	3.2	10
319	Fabrication of ordered FeNi nitride film with equiatomic Fe/Ni ratio. *Japanese Journal of Applied Physics*, **2018**, 57, 058004	1.4	8
318	Investigation of electrically active defects in undoped BaSi2 light absorber layers using deep-level transient spectroscopy. *Japanese Journal of Applied Physics*, **2018**, 57, 075801	1.4	8
317	Spectroscopic evidence of photogenerated carrier separation by built-in electric field in Sb-doped n-BaSi2/B-doped p-BaSi2homojunction diodes. *Japanese Journal of Applied Physics*, **2018**, 57, 050310	1.4	14
316	Identification of Vibrational Modes in BaSi2 Epitaxial Films by Infrared and Raman Spectroscopy. *Defect and Diffusion Forum*, **2018**, 386, 43-47	0.7	17
315	Temperature independent, wide modulation of anomalous Hall effect by Mn doping in Fe4−x Mn x N pseudo-single-crystal films. *Japanese Journal of Applied Physics*, **2018**, 57, 120305	1.4	5
314	Growth of tr6-CaSi2 thin films on Si(111) substrates. *Japanese Journal of Applied Physics*, **2018**, 57, 120312	1.4	5
313	Millimeter-sized magnetic domains in perpendicularly magnetized ferrimagnetic Mn4N thin films grown on SrTiO3. *Japanese Journal of Applied Physics*, **2018**, 57, 120310	1.4	16
312	Metal Catalysts for Layer-Exchange Growth of Multilayer Graphene. *ACS Applied Materials & Interfaces*, **2018**, 10, 41664-41669	9.5	16

311	Significant photoresponsivity enhancement of polycrystalline BaSi2 films formed on heated Si(111) substrates by sputtering. *Applied Physics Express*, **2018**, 11, 071401	2.4	15
310	Improving carrier mobility of polycrystalline Ge by Sn doping. *Scientific Reports*, **2018**, 8, 14832	4.9	28
309	Transition from minority to majority spin transport in iron-manganese nitride Fe4MnxN films with increasing x. *Journal of Applied Physics*, **2018**, 124, 123905	2.5	8
308	Improving the photoresponse spectra of BaSi2 layers by capping with hydrogenated amorphous Si layers prepared by radio-frequency hydrogen plasma. *AIP Advances*, **2018**, 8, 055306	1.5	7
307	Effect of BaSi2template growth duration on the generation of defects and performance of p-BaSi2/n-Si heterojunction solar cells. *Japanese Journal of Applied Physics*, **2018**, 57, 042301	1.4	4
306	Thermoelectric Inorganic SiGe Film Synthesized on Flexible Plastic Substrate. *ACS Applied Energy Materials*, **2018**,	6.1	17
305	High-hole mobility Si1-xGex (0.1 x 1) on an insulator formed by advanced solid-phase crystallization. *Journal of Alloys and Compounds*, **2018**, 766, 417-420	5.7	9
304	Direct synthesis of multilayer graphene on an insulator by Ni-induced layer exchange growth of amorphous carbon. *Applied Physics Letters*, **2017**, 110, 033108	3.4	24
303	Highly oriented epitaxial (2+2)-Fe 16 N 2 films on Fe(001) buffered MgAl 2 O 4 (001) substrates and their magnetization. *Journal of Crystal Growth*, **2017**, 468, 691-695	1.6	3
302	Exploring the potential of semiconducting BaSi2for thin-film solar cell applications. *Journal Physics D: Applied Physics*, **2017**, 50, 023001	3	69
301	Negative anisotropic magnetoresistance resulting from minority spin transport in NixFe4N (x = 1 and 3) epitaxial films. *Journal of Applied Physics*, **2017**, 121, 023903	2.5	17
300	Effects of Al grain size on metal-induced layer exchange growth of amorphous Ge thin film on glass substrate. *Thin Solid Films*, **2017**, 626, 190-193	2.2	5
299	Control of grain size and crystallinity of poly-Si films on quartz by Al-induced crystallization. *CrystEngComm*, **2017**, 19, 2305-2311	3.3	19
298	Fabrication and characterizations of nitrogen-doped BaSi2 epitaxial films grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2017**, 471, 37-41	1.6	
297	Effect of p-BaSi2layer thickness on the solar cell performance of p-BaSi2/n-Si heterojunction solar cells. *Japanese Journal of Applied Physics*, **2017**, 56, 05DB03	1.4	14
296	Boron-doped p-BaSi2/n-Si solar cells formed on textured n-Si(0 0 1) with a pyramid structure consisting of {1 1 1} facets. *Journal of Crystal Growth*, **2017**, 475, 186-191	1.6	6
295	Donor and acceptor levels in impurity-doped semiconducting BaSi2 thin films for solar-cell application. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1700019	1.6	8
294	Enhanced spectral response of semiconducting BaSi2 films by oxygen incorporation. *Thin Solid Films*, **2017**, 629, 17-21	2.2	10

293	Donor and acceptor energy levels in impurity Sb-, In-, Ag- and Cu-doped semiconducting BaSi2 thin films for device applications. *Energy Procedia*, **2017**, 124, 612-620	2.3	2
292	Growth of BaSi2 continuous films on Ge(111) by molecular beam epitaxy and fabrication of p-BaSi2/n-Ge heterojunction solar cells. *Japanese Journal of Applied Physics*, **2017**, 56, 05DB02	1.4	7
291	Polarized Raman spectra of BaSi2epitaxial film grown by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2017**, 56, 05DD02	1.4	11
290	GRAIN EFFECT IN THE CARRIER MOBILITY OF BaSi2 NANOFILMS **2017**, 38-41		
289	Postannealing effects on undoped BaSi2evaporated films grown on Si substrates. *Japanese Journal of Applied Physics*, **2017**, 56, 05DB05	1.4	16
288	Minority-carrier lifetime and photoresponse properties of B-doped p-BaSi2, a potential light absorber for solar cells. *Japanese Journal of Applied Physics*, **2017**, 56, 05DB01	1.4	5
287	Low temperature synthesis of highly oriented p-type Si1-xGex (x: 0□1) on an insulator by Al-induced layer exchange. *Journal of Applied Physics*, **2017**, 122, 155305	2.5	17
286	Magnetic domain walls in nanostrips of single-crystalline Fe4N(001) thin films with fourfold in-plane magnetic anisotropy. *Journal of Applied Physics*, **2017**, 121, 243904	2.5	12
285	High-quality multilayer graphene on an insulator formed by diffusion controlled Ni-induced layer exchange. *Applied Physics Letters*, **2017**, 111, 243104	3.4	20
284	Multilayer graphene on insulator formed by Co-induced layer exchange. *Japanese Journal of Applied Physics*, **2017**, 56, 05DE03	1.4	8
283	Effect of interlayer on silver-induced layer exchange crystallization of amorphous germanium thin film on insulator. *Japanese Journal of Applied Physics*, **2017**, 56, 05DE04	1.4	4
282	High-hole mobility polycrystalline Ge on an insulator formed by controlling precursor atomic density for solid-phase crystallization. *Scientific Reports*, **2017**, 7, 16981	4.9	51
281	Silver-induced layer exchange for polycrystalline germanium on a flexible plastic substrate. *Journal of Applied Physics*, **2017**, 122, 215305	2.5	12
280	Growth of BaSi2film on Ge(100) by vacuum evaporation and its photoresponse properties. *Japanese Journal of Applied Physics*, **2017**, 56, 05DB06	1.4	5
279	Controlling magnetic domain wall positions with an external magnetic field and a low spin-polarized current in chamfered L-shaped ferromagnetic thin ribbons. *Journal Physics D: Applied Physics*, **2016**, 49, 385002	3	4
278	Photoresponse properties of BaSi2film grown on Si (100) by vacuum evaporation. *Materials Research Express*, **2016**, 3, 076204	1.7	17
277	Perpendicular magnetic anisotropy in CoxMn4□N (x = 0 and 0.2) epitaxial films and possibility of tetragonal Mn4N phase. *AIP Advances*, **2016**, 6, 056201	1.5	25
276	Orientation control of intermediate-composition SiGe on insulator by low-temperature Al-induced crystallization. *Scripta Materialia*, **2016**, 122, 86-88	5.6	14

275	Control of electrical properties of BaSi2 thin films by alkali-metal doping using alkali-metal fluorides. *Thin Solid Films*, **2016**, 603, 218-223	2.2	6
274	Simple Vacuum Evaporation Route to BaSi2 Thin Films for Solar Cell Applications. *Procedia Engineering*, **2016**, 141, 27-31		17
273	On the Mechanism of BaSi2 Thin Film Formation on Si Substrate by Vacuum Evaporation. *Procedia Engineering*, **2016**, 141, 23-26		19
272	Effects of deposition rate on the structure and electron density of evaporated BaSi2 films. *Journal of Applied Physics*, **2016**, 120, 045103	2.5	26
271	Evaluation of band offset at amorphous-Si/BaSi2 interfaces by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2016**, 119, 165304	2.5	23
270	Effect of amorphous Si capping layer on the hole transport properties of BaSi2 and improved conversion efficiency approaching 10% in p-BaSi2/n-Si solar cells. *Applied Physics Letters*, **2016**, 109, 072103	3.4	82
269	Measurement of valence-band offset at native oxide/BaSi2 interfaces by hard x-ray photoelectron spectroscopy. *Journal of Applied Physics*, **2016**, 119, 025306	2.5	17
268	Electrical detection of magnetic domain wall in Fe4N nanostrip by negative anisotropic magnetoresistance effect. *Journal of Applied Physics*, **2016**, 120, 113903	2.5	1
267	First-principles study of twin grain boundaries in epitaxial BaSi2 on Si(111). *Journal of Applied Physics*, **2016**, 120, 085311	2.5	21
266	p-BaSi2/n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. *Applied Physics Letters*, **2016**, 108, 152101	3.4	62
265	Influence of air exposure duration and a-Si capping layer thickness on the performance of p-BaSi2/n-Si heterojunction solar cells. *AIP Advances*, **2016**, 6, 085107	1.5	34
264	Epitaxial growth and magnetic properties of NixFe4-xN (x = 0, 1, 3, and 4) films on SrTiO3(001) substrates. *Journal of Applied Physics*, **2016**, 120, 083907	2.5	12
263	Effect of oxygen incorporation in the Mg2Si lattice on its conductivity type □A possible reason of the p-type conductivity of postannealed Mg2Si thin film. *Journal of Alloys and Compounds*, **2016**, 676, 91-95	5.7	11
262	Sn-inserted Al-induced layer exchange for large-grained GeSn thin films on insulator. *Thin Solid Films*, **2016**, 616, 316-319	2.2	1
261	Growth and magnetic properties of epitaxial Fe4N films on insulators possessing lattice spacing close to Si(001) plane. *Journal of Crystal Growth*, **2016**, 455, 66-70	1.6	7
260	Fabrication of L-shaped Fe4N ferromagnetic narrow wires and position control of magnetic domain wall with magnetic field. *Japanese Journal of Applied Physics*, **2015**, 54, 028003	1.4	3
259	Cross-sectional potential profile across a BaSi2pn junction by Kelvin probe force microscopy. *Japanese Journal of Applied Physics*, **2015**, 54, 030306	1.4	3
258	Local electronic states of Fe4N films revealed by x-ray absorption spectroscopy and x-ray magnetic circular dichroism. *Journal of Applied Physics*, **2015**, 117, 193906	2.5	16

257	Vertically Aligned Ge Nanowires on Flexible Plastic Films Synthesized by (111)-Oriented Ge Seeded Vapor-Liquid-Solid Growth. *ACS Applied Materials & Interfaces*, **2015**, 7, 18120-4	9.5	19
256	Effects of flexible substrate thickness on Al-induced crystallization of amorphous Ge thin films. *Thin Solid Films*, **2015**, 583, 221-225	2.2	8
255	70 °C synthesis of high-Sn content (25%) GeSn on insulator by Sn-induced crystallization of amorphous Ge. *Applied Physics Letters*, **2015**, 106, 082109	3.4	55
254	Mössbauer study on epitaxial CoxFe4−xN films grown by molecular beam epitaxy. *Journal of Applied Physics*, **2015**, 117, 17B717	2.5	5
253	Effect of Diffusion Control Layer on Reverse Al-Induced Layer Exchange Process for High-Quality Ge/Al/Glass Structure. *Journal of Electronic Materials*, **2015**, 44, 1377-1381	1.9	1
252	Formation of BaSi2 heterojunction solar cells using transparent MoOx hole transport layers. *Applied Physics Letters*, **2015**, 106, 122104	3.4	15
251	Structural and electrical characterizations of crack-free BaSi2 thin films fabricated by thermal evaporation. *Thin Solid Films*, **2015**, 595, 68-72	2.2	27
250	Characterization of defect levels in undoped n-BaSi2epitaxial films on Si(111) by deep-level transient spectroscopy. *Japanese Journal of Applied Physics*, **2015**, 54, 07JE01	1.4	9
249	Transfer-free synthesis of highly ordered Ge nanowire arrays on glass substrates. *Applied Physics Letters*, **2015**, 107, 133102	3.4	6
248	Influence of Substrate on Crystal Orientation of Large-Grained Si Thin Films Formed by Metal-Induced Crystallization. *International Journal of Photoenergy*, **2015**, 2015, 1-7	2.1	10
247	Possibility of Si-based new material for thin-film solar cell applications. *Journal of Physics: Conference Series*, **2015**, 596, 012005	0.3	3
246	Realization of single-phase BaSi2films by vacuum evaporation with suitable optical properties and carrier lifetime for solar cell applications. *Japanese Journal of Applied Physics*, **2015**, 54, 07JE02	1.4	32
245	Fabrication of single-phase polycrystalline BaSi2thin films on silicon substrates by vacuum evaporation for solar cell applications. *Japanese Journal of Applied Physics*, **2015**, 54, 08KC03	1.4	24
244	Exploring the possibility of semiconducting BaSi2for thin-film solar cell applications. *Japanese Journal of Applied Physics*, **2015**, 54, 07JA01	1.4	76
243	**2015**,		1
242	Improved Surface Quality of the Metal-Induced Crystallized Ge Seed Layer and Its Influence on Subsequent Epitaxy. *Crystal Growth and Design*, **2015**, 15, 1535-1539	3.5	26
241	Energetic evaluation of possible interstitial compound formation of BaSi2with 2p-, 3s-, and 3d-elements using first-principle calculations. *Japanese Journal of Applied Physics*, **2015**, 54, 07JE03	1.4	3
240	Potential variations around grain boundaries in impurity-doped BaSi2 epitaxial films evaluated by Kelvin probe force microscopy. *Journal of Applied Physics*, **2014**, 116, 123709	2.5	20

239	Diffusion coefficients of impurity atoms in BaSi2epitaxial films grown by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2014**, 53, 04ER02	1.4	7
238	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi2 on Si(111). *Journal of Applied Physics*, **2014**, 115, 193510	2.5	64
237	N-type doping of BaSi2 epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. *Thin Solid Films*, **2014**, 567, 105-108	2.2	20
236	Direct synthesis of highly textured Ge on flexible polyimide films by metal-induced crystallization. *Applied Physics Letters*, **2014**, 104, 262107	3.4	17
235	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. *CrystEngComm*, **2014**, 16, 2578	3.3	17
234	Self-organization of Ge(111)/Al/glass structures through layer exchange in metal-induced crystallization. *CrystEngComm*, **2014**, 16, 9590-9595	3.3	8
233	Toward Si-based high-efficiency thin-film solar cells using semiconducting BaSi2. *IOP Conference Series: Materials Science and Engineering*, **2014**, 54, 012009	0.4	1
232	Precipitation control and activation enhancement in boron-doped p+-BaSi2 films grown by molecular beam epitaxy. *Applied Physics Letters*, **2014**, 104, 252104	3.4	27
231	Analysis of the electrical properties of Cr/n-BaSi2 Schottky junction and n-BaSi2/p-Si heterojunction diodes for solar cell applications. *Journal of Applied Physics*, **2014**, 115, 223701	2.5	41
230	Evaluation of minority carrier diffusion length of undoped n-BaSi2epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. *Japanese Journal of Applied Physics*, **2014**, 53, 078004	1.4	16
229	Growth promotion of Al-induced crystallized Ge films on insulators by insertion of a Ge membrane below the Al layer. *Thin Solid Films*, **2014**, 557, 143-146	2.2	12
228	Large-grained (111)-oriented Si/Al/SiO2 structures formed by diffusion-controlled Al-induced layer exchange. *Thin Solid Films*, **2014**, 557, 147-150	2.2	6
227	N-type doping of BaSi2 epitaxial films by phosphorus ion implantation and thermal annealing. *Thin Solid Films*, **2014**, 557, 90-93	2.2	23
226	Fabrication and characterization of BaSi2epitaxial films over 1 μm in thickness on Si(111). *Japanese Journal of Applied Physics*, **2014**, 53, 04ER04	1.4	29
225	Potential variation around grain boundaries in BaSi2 films grown on multicrystalline silicon evaluated using Kelvin probe force microscopy. *Journal of Applied Physics*, **2014**, 116, 235301	2.5	6
224	Low-temperature (180 °C) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. *Applied Physics Letters*, **2014**, 104, 022106	3.4	88
223	Photoresponse properties of undoped BaSi2epitaxial layers on n+-BaSi2/p+-Si(001) by molecular beam epitaxy. *Japanese Journal of Applied Physics*, **2014**, 53, 058007	1.4	14
222	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. *Journal of Applied Physics*, **2014**, 115, 094301	2.5	36

221	Sign of the spin-polarization in cobalt-iron nitride films determined by the anisotropic magnetoresistance effect. *Journal of Applied Physics*, **2014**, 116, 053912	2.5	35
220	Perpendicular magnetic anisotropy of Mn4N films on MgO(001) and SrTiO3(001) substrates. *Journal of Applied Physics*, **2014**, 115, 17A935	2.5	57
219	Al-induced crystallization of amorphous Ge thin films on conducting layer coated glass substrates. *Japanese Journal of Applied Physics*, **2014**, 53, 04EH01	1.4	6
218	Structural characterization of polycrystalline Ge thin films on insulators formed by diffusion-enhanced Al-induced layer exchange. *Japanese Journal of Applied Physics*, **2014**, 53, 04EH03	1.4	7
217	X-ray magnetic circular dichroism for CoxFe4−xN (x = 0, 3, 4) films grown by molecular beam epitaxy. *Journal of Applied Physics*, **2014**, 115, 17C712	2.5	18
216	Energetic stability and magnetic moment of tri-, tetra-, and octa- ferromagnetic element nitrides predicted by first-principle calculations. *Journal of Alloys and Compounds*, **2014**, 611, 440-445	5.7	19
215	Temperature dependent Al-induced crystallization of amorphous Ge thin films on SiO2 substrates. *Journal of Crystal Growth*, **2013**, 372, 189-192	1.6	13
214	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. *Crystal Growth and Design*, **2013**, 13, 1767-1770	3.5	43
213	Lattice and grain-boundary diffusions of boron atoms in BaSi2 epitaxial films on Si(111). *Journal of Applied Physics*, **2013**, 113, 053511	2.5	19
212	In-situ heavily p-type doping of over 1020 cm⁻³ in semiconducting BaSi2 thin films for solar cells applications. *Applied Physics Letters*, **2013**, 102, 112107	3.4	59
211	Effect of atomic-hydrogen irradiation on reduction of residual carrier concentration in β-FeSi2 films grown on Si substrates by atomic-hydrogen-assisted molecular beam epitaxy. *Journal of Crystal Growth*, **2013**, 378, 365-367	1.6	2
210	Possibility of spin-polarized electric current through Mn-, Fe-, Co-, or Ni-doped BaSi2 predicted by their calculated densities of states. *Journal of Magnetism and Magnetic Materials*, **2013**, 344, 25-29	2.8	2
209	Evaluation of diffusion coefficients of n-type impurities in MBE-grown BaSi2 epitaxial layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1762-1764		1
208	Molecular beam epitaxy of boron doped p-type BaSi2 epitaxial films on Si(111) substrates for thin-film solar cells. *Journal of Crystal Growth*, **2013**, 378, 201-204	1.6	13
207	Structural study on phosphorus doping of BaSi2 epitaxial films by ion implantation. *Thin Solid Films*, **2013**, 534, 470-473	2.2	15
206	Formation of polycrystalline BaSi2 films by radio-frequency magnetron sputtering for thin-film solar cell applications. *Thin Solid Films*, **2013**, 534, 116-119	2.2	26
205	Formation of large-grain-sized BaSi2 epitaxial layers grown on Si(111) by molecular beam epitaxy. *Journal of Crystal Growth*, **2013**, 378, 193-197	1.6	5
204	Epitaxial growth of ferromagnetic CoxFe4−xN thin films on SrTiO3 (001) and magneticproperties. *Journal of Crystal Growth*, **2013**, 378, 342-346	1.6	5

203	Lattice and grain-boundary diffusions of impurity atoms in BaSi2 epitaxial layers grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2013**, 378, 189-192	1.6	7
202	Large photoresponsivity in semiconducting BaSi2 epitaxial films grown on Si(001) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2013**, 378, 198-200	1.6	4
201	On the growth mechanism of polycrystalline silicon thin film by Al-induced layer exchange process. *Journal of Crystal Growth*, **2013**, 362, 16-19	1.6	8
200	Double-Layered Ge Thin Films on Insulators Formed by an Al-Induced Layer-Exchange Process. *Crystal Growth and Design*, **2013**, 13, 3908-3912	3.5	16
199	Large-Grained Polycrystalline (111) Ge Films on Insulators by Thickness-Controlled Al-Induced Crystallization. *ECS Journal of Solid State Science and Technology*, **2013**, 2, Q195-Q199	2	16
198	Electronic structures and magnetic moments of Co3FeN thin films grown by molecular beam epitaxy. *Applied Physics Letters*, **2013**, 103, 232403	3.4	10
197	Evaluation of potential variations around grain boundaries in BaSi2 epitaxial films by Kelvin probe force microscopy. *Applied Physics Letters*, **2013**, 103, 142113	3.4	26
196	Mechanism of strain relaxation in BaSi2 epitaxial films on Si(111) substrates during post-growth annealing and application for film exfoliation. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1677-1680		15
195	Determination of Bulk Minority-Carrier Lifetime in BaSi2Earth-Abundant Absorber Films by Utilizing a Drastic Enhancement of Carrier Lifetime by Post-Growth Annealing. *Applied Physics Express*, **2013**, 6, 112302	2.4	58
194	Fabrication and characterizations of phosphorus-doped n-type BaSi2 epitaxial films grown by molecular beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1753-1755		14
193	Hard x-ray photoelectron spectroscopy study on valence band structure of semiconducting BaSi2. *Journal of Applied Physics*, **2013**, 114, 123702	2.5	13
192	Investigation of the tunneling properties and surface morphologies of BaSi2/Si tunnel junctions for BaSi2 solar cell applications. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1765-1768		1
191	Effect of Ge/Al thickness on Al-induced crystallization of amorphous Ge layers on glass substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1781-1784		
190	Fabrication of n+-BaSi2/p+-Si tunnel junction on Si(001) surface for characterization of photoresponse properties of BaSi2epitaxial films. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1773-1776		
189	Fabrication of BaSi2 films on (111)-oriented Si layers formed by inverted Al-induced crystallization method on glass structure. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1769-1772		1
188	Epitaxial growth of BaSi2 films with large grains using vicinal Si(111) substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1756-1758		1
187	Fabrication and characterization of polycrystalline BaSi2 by RF sputtering. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1759-1761		39
186	Local structure around Sr in semiconducting BaSrSi2 studied using extended x-ray absorption fine structures. *Physics Procedia*, **2012**, 23, 53-56		1

185	Electrical characterization and conduction mechanism of impurity-doped BaSi2 films grown on Si(111) by molecular beam epitaxy. *Thin Solid Films*, **2012**, 522, 95-99	2.2	37
184	Highly (111)-oriented Ge thin films on insulators formed by Al-induced crystallization. *Applied Physics Letters*, **2012**, 101, 072106	3.4	78
183	Molecular beam epitaxy of BaSi2 thin films on Si(001) substrates. *Journal of Crystal Growth*, **2012**, 345, 16-21	1.6	53
182	Investigation of grain boundaries in BaSi2 epitaxial films on Si(1 1 1) substrates using transmission electron microscopy and electron-beam-induced current technique. *Journal of Crystal Growth*, **2012** , 348, 75-79	1.6	108
181	Dependence of crystal orientation in Al-induced crystallized poly-Si layers on SiO2 insertion layer thickness. *Journal of Crystal Growth*, **2012**, 356, 65-69	1.6	19
180	Molecular beam epitaxy of Co Fe4N (0.4. *Journal of Crystal Growth*, **2012**, 357, 53-57	1.6	11
179	Improved photoresponsivity of semiconducting BaSi2 epitaxial films grown on a tunnel junction for thin-film solar cells. *Applied Physics Letters*, **2012**, 100, 152114	3.4	42
178	Investigation of the recombination mechanism of excess carriers in undoped BaSi2 films on silicon. *Journal of Applied Physics*, **2012**, 112, 083108	2.5	75
177	Negative spin polarization at the Fermi level in Fe4N epitaxial films by spin-resolved photoelectron spectroscopy. *Journal of Applied Physics*, **2012**, 112, 013911	2.5	25
176	Realization of Large-Domain Barium Disilicide Epitaxial Thin Film by Introduction of Miscut to Si(111) Substrate. *Japanese Journal of Applied Physics*, **2012**, 51, 10NB06	1.4	2
175	Negative Anisotropic Magnetoresistance in $gammak$-Fe$_{4}$N Epitaxial Films on SrTiO$_{3}$(001) Grown by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2012**, 51, 068001	1.4	15
174	Effect of Solid-Phase-Epitaxy Si Layers on Suppression of Sb Diffusion from Sb-Doped n^{+}-BaSi$_{2}$/p^{+}-Si Tunnel Junction to Undoped BaSi$_{2}$ Overlayers. *Japanese Journal of Applied Physics*, **2012**, 51, 04DP01	1.4	1
173	Epitaxy of Orthorhombic BaSi$_{2}$ with Preferential In-Plane Crystal Orientation on Si(001): Effects of Vicinal Substrate and Annealing Temperature. *Japanese Journal of Applied Physics*, **2012**, 51, 095501	1.4	5
172	Molecular Beam Epitaxy of BaSi$_{2}$ Films with Grain Size over 4 mum on Si(111). *Japanese Journal of Applied Physics*, **2012**, 51, 098003	1.4	7
171	Effect of Solid-Phase-Epitaxy Si Layers on Suppression of Sb Diffusion from Sb-Doped n+-BaSi2/p+-Si Tunnel Junction to Undoped BaSi2Overlayers. *Japanese Journal of Applied Physics*, **2012**, 51, 04DP01	1.4	1
170	Negative Anisotropic Magnetoresistance in Fe4N Epitaxial Films on SrTiO3(001) Grown by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2012**, 51, 068001	1.4	8
169	Epitaxy of Orthorhombic BaSi2with Preferential In-Plane Crystal Orientation on Si(001): Effects of Vicinal Substrate and Annealing Temperature. *Japanese Journal of Applied Physics*, **2012**, 51, 095501	1.4	1
168	Realization of Large-Domain Barium Disilicide Epitaxial Thin Film by Introduction of Miscut to Si(111) Substrate. *Japanese Journal of Applied Physics*, **2012**, 51, 10NB06	1.4	1

167	Molecular Beam Epitaxy of BaSi2Films with Grain Size over 4 μm on Si(111). *Japanese Journal of Applied Physics*, **2012**, 51, 098003	1.4	6
166	Epitaxial growth and magnetic characterization of ferromagnetic Co4N thin films on SrTiO3(001) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2011**, 336, 40-43	1.6	32
165	Epitaxial growth of ferromagnetic Fe4N thin films on SrTiO3(001) substrates by molecular beam epitaxy. *Journal of Physics: Conference Series*, **2011**, 266, 012091	0.3	3
164	Room temperature magnetoresistance in Fe3Si/CaF2/Fe3Si MTJ epitaxially grown on Si(111). *Journal of Physics: Conference Series*, **2011**, 266, 012088	0.3	6
163	Fabrication of Fe3Si/CaF2 heterostructures ferromagnetic resonant tunneling diode by selected-area molecular beam epitaxy. *Thin Solid Films*, **2011**, 519, 8509-8511	2.2	1
162	Photoresponse properties of BaSi2 epitaxial films grown on the tunnel junction for high-efficiency thin-film solar cells. *Thin Solid Films*, **2011**, 519, 8501-8504	2.2	16
161	Metalorganic chemical vapor deposition of β-FeSi2 on β-FeSi2 seed crystals formed on Si substrates. *Thin Solid Films*, **2011**, 519, 8473-8476	2.2	1
160	Al- and Cu-doped . *Physics Procedia*, **2011**, 11, 11-14		25
159	Magnetoresistance characteristics of . *Physics Procedia*, **2011**, 11, 15-18		1
158	Reduction of carrier concentrations of . *Physics Procedia*, **2011**, 11, 19-22		
157	Molecular beam epitaxy of β-FeSi2 films on Si(111) substrates and its influence on minority-carrier diffusion length of Si measured by EBIC. *Physics Procedia*, **2011**, 11, 23-26		
156	Growth of Al-doped p-type BaSi2 films by molecular beam epitaxy and the effect of high-temperature annealing on their electrical properties. *Physics Procedia*, **2011**, 11, 27-30		27
155	Formation of poly-Si layers on AZO/. *Physics Procedia*, **2011**, 11, 31-34		3
154	Fabrication of BaSi2 films on transparent CaF2 (111) substrates by molecular beam epitaxy for optical characterization. *Physics Procedia*, **2011**, 11, 189-192		2
153	Structural control of organic solar cells based on nonplanar metallophthalocyanine/C60 heterojunctions using organic buffer layers. *Organic Electronics*, **2011**, 12, 966-973	3.5	28
152	Toward the epitaxial growth of ferromagnetic . *Physics Procedia*, **2011**, 11, 193-195		
151	Molecular beam epitaxy of ferromagnetic γ-Fe4N thin films on LaAlO3(1 0 0), SrTiO3(1 0 0) and MgO(1 0 0) substrates. *Journal of Crystal Growth*, **2011**, 322, 63-68	1.6	36
150	In situObservation of Polycrystalline Silicon Thin Films Grown Using Aluminum-Doped Zinc Oxide on Glass Substrate by the Aluminum-Induced Crystallization. *Japanese Journal of Applied Physics*, **2011**, 50, 04DP02	1.4	1

149	Optical Absorption Properties of BaSi2Epitaxial Films Grown on a Transparent Silicon-on-Insulator Substrate Using Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 068001	1.4	65
148	Dependence of Resonant Voltage on Quantum-Well Width in CaF$_{2}$/Fe$_{3}$Si/CaF$_{2}$ Resonant Tunneling Diodes. *Japanese Journal of Applied Physics*, **2011**, 50, 108002	1.4	2
147	Effect of Introducing FeSi2Template Layers on Defect Density and Minority Carrier Diffusion Length in Si Region near p-FeSi2/n-Si Heterointerface. *Japanese Journal of Applied Physics*, **2011**, 50, 041303	1.4	
146	X-ray magnetic circular dichroism of ferromagnetic Co4N epitaxial films on SrTiO3(001) substrates grown by molecular beam epitaxy. *Applied Physics Letters*, **2011**, 99, 252501	3.4	22
145	Spin and orbital magnetic moments of molecular beam epitaxy -Fe4N films on LaAlO3(001) and MgO(001) substrates by x-ray magnetic circular dichroism. *Applied Physics Letters*, **2011**, 98, 102507	3.4	35
144	Minority-carrier diffusion length, minority-carrier lifetime, and photoresponsivity of FeSi2 layers grown by molecular-beam epitaxy. *Journal of Applied Physics*, **2011**, 109, 123502	2.5	9
143	Molecular Beam Epitaxy of Cu-Doped BaSi2 Films on Si(111) Substrate and Evaluation & Qualification of Depth Profiles of Cu Atoms for the Formation of Efficient Solar Cells. *Advanced Materials Research*, **2011**, 326, 139-143	0.5	3
142	Structural Study of BF$_{2}$ Ion Implantation and Post Annealing of BaSi$_{2}$ Epitaxial Films. *Japanese Journal of Applied Physics*, **2011**, 50, 121202	1.4	6
141	In situObservation of Polycrystalline Silicon Thin Films Grown Using Aluminum-Doped Zinc Oxide on Glass Substrate by the Aluminum-Induced Crystallization. *Japanese Journal of Applied Physics*, **2011**, 50, 04DP02	1.4	5
140	Optical Absorption Properties of BaSi2Epitaxial Films Grown on a Transparent Silicon-on-Insulator Substrate Using Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2011**, 50, 068001	1.4	56
139	Effect of Introducing FeSi2Template Layers on Defect Density and Minority Carrier Diffusion Length in Si Region near p-FeSi2/n-Si Heterointerface. *Japanese Journal of Applied Physics*, **2011**, 50, 041303	1.4	
138	Dependence of Resonant Voltage on Quantum-Well Width in CaF2/Fe3Si/CaF2Resonant Tunneling Diodes. *Japanese Journal of Applied Physics*, **2011**, 50, 108002	1.4	
137	Structural Study of BF2Ion Implantation and Post Annealing of BaSi2Epitaxial Films. *Japanese Journal of Applied Physics*, **2011**, 50, 121202	1.4	2
136	On the Controlling Mechanism of Preferential Orientation of Polycrystalline-Silicon Thin Films Grown by Aluminum-Induced Crystallization. *Applied Physics Express*, **2010**, 3, 095803	2.4	29
135	Epitaxial Growth and Photoresponse Properties of BaSi2Layers toward Si-Based High-Efficiency Solar Cells. *Japanese Journal of Applied Physics*, **2010**, 49, 04DP05	1.4	6
134	Impact of Thin Island-Like BaSi2Template on the Formation of n+-BaSi2/p+-Si Tunnel Junction on Si(111) Surface by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2010**, 49, 068001	1.4	7
133	Improved Reproducibility in CaF2/Fe3Si/CaF2Ferromagnetic Resonant Tunneling Diodes on Si(111) Substrates by Selected-Area Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2010**, 49, 060212	1.4	8
132	Enhanced Room-Temperature 1.6 m Electroluminescence from Si-Based Double-Heterostructure Light-Emitting Diodes Using Iron Disilicide. *Japanese Journal of Applied Physics*, **2010**, 49, 04DG16	1.4	9

131	Fabrication of n+-BaSi2/p+-Si Tunnel Junction on Si(111) Surface by Molecular Beam Epitaxy for Photovoltaic Applications. *Applied Physics Express*, **2010**, 3, 021301	2.4	28
130	Impact of amorphous Ge thin layer at the amorphous Si/Al interface on Al-induced crystallization. *Journal of Crystal Growth*, **2010**, 312, 3257-3260	1.6	5
129	p-Si/β-FeSi2/n-Si double-heterostructure light-emitting diodes achieving 1.6 μm electroluminescence of 0.4 mW at room temperature. *Applied Physics Letters*, **2009**, 94, 213509	3.4	24
128	Spin polarization of Fe4N thin films determined by point-contact Andreev reflection. *Applied Physics Letters*, **2009**, 94, 202502	3.4	57
127	Wet Chemical Etching and X-ray Photoelectron Spectroscopy Analysis of BaSi2Epitaxial Films Grown by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2009**, 48, 106507	1.4	3
126	Growth of manganese silicide layers on Si substrates using MnCl2 source. *Physica Status Solidi (A) Applications and Materials Science*, **2009**, 206, 233-237	1.6	8
125	Growth of ferromagnetic Fe4N epitaxial layers and a-axis-oriented Fe4N/MgO/Fe magnetic tunnel junction on MgO(001) substrates using molecular beam epitaxy. *Journal of Crystal Growth*, **2009**, 311, 1616-1619	1.6	15
124	Fabrication of (111)-oriented Si layers on SiO2 substrates by an aluminum-induced crystallization method and subsequent growth of semiconducting BaSi2 layers for photovoltaic application. *Journal of Crystal Growth*, **2009**, 311, 3581-3586	1.6	29
123	CaF2/Fe3Si/CaF2Ferromagnetic Resonant Tunneling Diodes on Si(111) by Molecular Beam Epitaxy. *Applied Physics Express*, **2009**, 2, 063006	2.4	12
122	Photoresponse Properties of Polycrystalline BaSi2Films Grown on SiO2Substrates Using (111)-Oriented Si Layers by an Aluminum-Induced Crystallization Method. *Applied Physics Express*, **2009**, 2, 051601	2.4	52
121	Photoresponse Properties of Semiconducting BaSi2Epitaxial Films Grown on Si(111) Substrates by Molecular Beam Epitaxy. *Applied Physics Express*, **2009**, 2, 021101	2.4	52
120	Growth of Ca-Germanide and Ca-Silicide Crystals by Mechanical Alloying. *E-Journal of Surface Science and Nanotechnology*, **2009**, 7, 129-133	0.7	5
119	Fabrication and Current–Voltage Characteristics of Fe3Si/CaF2/Fe3Si Magnetic Tunnel Junction. *Japanese Journal of Applied Physics*, **2008**, 47, 6310-6311	1.4	12
118	Room-Temperature 1.6 μm Electroluminescence fromp+-Si/β-FeSi2/n+-Si Diodes on Si(001) without High-Temperature Annealing. *Applied Physics Express*, **2008**, 1, 051405	2.4	7
117	Control of Electron and Hole Concentrations in Semiconducting Silicide BaSi2with Impurities Grown by Molecular Beam Epitaxy. *Applied Physics Express*, **2008**, 1, 051403	2.4	58
116	Sb Surfactant Effect on Defect Evolution in Compressively Strained In0.80Ga0.20As Quantum Well on InP Grown by Metalorganic Vapor Phase Epitaxy. *Applied Physics Express*, **2008**, 1, 111202	2.4	6
115	Improved Room-Temperature 1.6 μm Electroluminescence fromp-Si/β-FeSi2/n-Si Double Heterostructures Light-Emitting Diodes. *Applied Physics Express*, **2008**, 1, 021403	2.4	17
114	Evaluation of minority-carrier diffusion length in n-type β-FeSi2 single crystals by electron-beam-induced current. *Applied Physics Letters*, **2008**, 92, 042117	3.4	14

113	Lifetime and diffusion length of photogenerated minority carriers in single-crystalline n-type □FeSi2 bulk. *Applied Physics Letters*, **2008**, 92, 192114	3.4	15
112	Semiconductor(BaSi2)/metal(CoSi2) Schottky-barrier structures epitaxially grown on Si(111) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2008**, 310, 1250-1255	1.6	8
111	Molecular beam epitaxy of semiconductor (BaSi2)/metal (CoSi2) hybrid structures on Si(1 1 1) substrates for photovoltaic application. *Applied Surface Science*, **2008**, 254, 7963-7967	6.7	2
110	Inductively coupled plasma-reactive ion etching for □FeSi2 film. *Thin Solid Films*, **2007**, 515, 8166-8168	2.2	1
109	Effects of Sr addition on crystallinity and optical absorption edges in ternary semiconducting silicide Ba1□SrxSi2. *Thin Solid Films*, **2007**, 515, 8216-8218	2.2	12
108	Epitaxial growth of Fe3Si/CaF2/Fe3Si magnetic tunnel junction structures on CaF2/Si(111) by molecular beam epitaxy. *Thin Solid Films*, **2007**, 515, 8254-8258	2.2	8
107	Preparation of □FeSi2 substrates by molten salt method. *Thin Solid Films*, **2007**, 515, 8268-8271	2.2	11
106	Epitaxial growth of ferromagnetic Fe3N films on Si(111) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2007**, 301-302, 597-601	1.6	31
105	Epitaxial growth and luminescence characterization of Si/□FeSi2/Si multilayered structures by molecular beam epitaxy. *Journal of Crystal Growth*, **2007**, 301-302, 676-679	1.6	18
104	Molecular beam epitaxy of band gap tunable ternary semiconducting silicides Ba1□SrxSi2 for photovoltaic application. *Journal of Crystal Growth*, **2007**, 301-302, 680-683	1.6	23
103	Growth of highly oriented crystalline □Fe/AlN/Fe3N trilayer structures on Si(111) substrates by molecular beam epitaxy. *Journal of Crystal Growth*, **2007**, 309, 25-29	1.6	9
102	Growth and characterization of group-III impurity-doped semiconducting BaSi2 films grown by molecular beam epitaxy. *Thin Solid Films*, **2007**, 515, 8242-8245	2.2	27
101	Investigation of current injection in □FeSi2/Si double-heterostructures light-emitting diodes by molecular beam epitaxy. *Thin Solid Films*, **2007**, 515, 8136-8139	2.2	4
100	Growth of Nitride-Based Fe3N/AlN/Fe4N Magnetic Tunnel Junction Structures on Si(111) Substrates. *Japanese Journal of Applied Physics*, **2007**, 46, L892-L894	1.4	7
99	Epitaxial Growth and Magnetic Properties of Fe3Si/CaF2/Fe3Si Tunnel Junction Structures on CaF2/Si(111). *Japanese Journal of Applied Physics*, **2007**, 46, L904-L906	1.4	10
98	Photoresponse properties of Al□-□FeSi2 Schottky diodes using □FeSi2 single crystals. *Applied Physics Letters*, **2007**, 91, 142114	3.4	26
97	Effect of using a high-purity Fe source on the transport properties of p-type □FeSi2 grown by molecular-beam epitaxy. *Journal of Applied Physics*, **2007**, 102, 103706	2.5	21
96	Photoluminescence decay time and electroluminescence of p-Si□FeSi2 particles□-Si and p-Si□FeSi2 film□-Si double-heterostructures light-emitting diodes grown by molecular-beam epitaxy. *Journal of Applied Physics*, **2007**, 101, 124506	2.5	25

95	Annealing temperature dependence of EL properties of Si/β-FeSi2/Si(111) double-heterostructures light-emitting diodes. *Thin Solid Films*, **2006**, 508, 376-379	2.2	13
94	Epitaxial growth and characterization of Si-based light-emitting Si/β-FeSi2 film/Si double heterostructures on Si(001) substrates by molecular beam epitaxy. *Thin Solid Films*, **2006**, 508, 371-375	2.2	26
93	Optical and electrical properties of semiconducting BaSi2 thin films on Si substrates grown by molecular beam epitaxy. *Thin Solid Films*, **2006**, 508, 363-366	2.2	165
92	Optical Absorption Edge of Ternary Semiconducting Silicide Ba1-xSrxSi2. *Japanese Journal of Applied Physics*, **2006**, 45, L390-L392	1.4	56
91	Epitaxial Growth and Magnetic Properties of Ferromagnetic Fe3N on Si(111) by Molecular Beam Epitaxy Using AlN/3C-SiC Intermediate Layers. *Japanese Journal of Applied Physics*, **2006**, 45, L705-L707	1.4	9
90	Reactive Ion Etching of β-FeSi2with Inductively Coupled Plasma. *Japanese Journal of Applied Physics* , **2006**, 45, L569-L571	1.4	2
89	Epitaxial Growth and Luminescence Characterization of Si-based Double Heterostructures Light-emitting Diodes with Iron Disilicide Active Region. *Materials Research Society Symposia Proceedings*, **2006**, 958, 1		
88	Crystal Growth of β-FeSi2 Thin Film on (100), (110) and (111) Plane of Si and Yittria-stabilized Zirconia Substrates. *Materials Research Society Symposia Proceedings*, **2006**, 980, 47		
87	Temperature dependence of electroluminescence from silicon p-i-n light-emitting diodes. *Journal of Applied Physics*, **2006**, 100, 023506	2.5	5
86	Band Diagrams of BaSi2/Si Structure by Kelvin Probe and Current-Voltage Characteristics. *Japanese Journal of Applied Physics*, **2006**, 45, L519-L521	1.4	58
85	Horizontal growth of epitaxial (100) β-FeSi2 templates by metal–organic chemical vapor deposition. *Journal of Crystal Growth*, **2006**, 287, 694-697	1.6	3
84	Improvement of luminescence from β-FeSi2 particles embedded in silicon, with high temperature silicon buffer layer. *Journal of Crystal Growth*, **2006**, 290, 176-179	1.6	1
83	Temperature dependence of electroluminescence from Si-based light emitting diodes with β-FeSi2 particles active region. *Journal of Luminescence*, **2006**, 118, 330-334	3.8	4
82	Epitaxial growth of Fe3Si/CaF2/Si(111) hybrid structures by molecular beam epitaxy. *Thin Solid Films*, **2006**, 508, 78-81	2.2	19
81	Cr concentration dependence of magnetic and electrical properties of Cr-doped GaN films on Si (111) by MOMBE. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 2488-2491		3
80	Magneto-Optical Studies of Ferromagnetic Cr-Doped GaN Films Grown by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2005**, 44, 6510-6512	1.4	5
79	Epitaxial Growth of Ferromagnetic Fe3Si Films on CaF2/Si(111) by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2005**, 44, L715-L717	1.4	13
78	Growth and Characterization of Si-Based Light-Emitting Diode with β-FeSi2-Particles/Si Multilayered Active Region by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2005**, 44, 3951-3953	1.4	22

77	Fabrication of p-Si/β-FeSi2/n-Si Double-Heterostructure Light-Emitting Diode by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2005**, 44, 2483-2486	1.4	23
76	Room-temperature electroluminescence of a Si-based p-i-n diode with β-FeSi2 particles embedded in the intrinsic silicon. *Journal of Applied Physics*, **2005**, 97, 043529	2.5	26
75	Hole mobility of p-type β-FeSi2 thin films grown from Si-Ge multilayers. *Journal of Applied Physics*, **2005**, 97, 093716	2.5	22
74	Disagreement between Magnetic and Magneto-Optical Properties in Cr-doped GaN Films on Si(111) Substrates Grown by Metal Organic Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2004**, 43, L1312-L1314	1.4	7
73	Time-Resolved Photoluminescence Study of Si/β-FeSi2/Si Structures Grown by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2004**, 43, L930-L933	1.4	14
72	Epitaxial Growth of Si-Based Ternary Alloy Semiconductor Ba1-xSrxSi2Films on Si(111) Substrates by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2004**, 43, L771-L773	1.4	34
71	Thermal Enhancement of 1.6 μm Electroluminescence from a Si-Based Light-Emitting Diode with β-FeSi2Active Region. *Japanese Journal of Applied Physics*, **2004**, 43, L1492-L1494	1.4	4
70	Molecular Beam Epitaxy of Highly [100]-Oriented β-FeSi2Films on Lattice-Matched Strained-Si(001) Surface Using Si0.7Ge0.3Layers. *Japanese Journal of Applied Physics*, **2004**, 43, L957-L959	1.4	8
69	Growth of Si-β-FeSi2-Si double-heterostructures on Si(111) substrates by molecular-beam epitaxy and photoluminescence using time-resolved measurements. *Journal of Applied Physics*, **2004**, 96, 2561-2565	2.5	35
68	Influence of β-FeSi2 particle size and Si growth rate on 1.5 μm photoluminescence from Si/β-FeSi2-particles/Si structures grown by molecular-beam epitaxy. *Journal of Applied Physics*, **2004**, 95, 5483-5486	2.5	15
67	Influence of AlN Growth Conditions on the Polarity of GaN Grown on AlN/Si(111) by Metalorganic Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2004**, 43, L151-L153	1.4	7
66	Growth of Epitaxial β-FeSi2Thin Film on Si(001) by Metal-Organic Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2004**, 43, L551-L553	1.4	27
65	Tolerance of GaAs as an original substrate for HVPE growth of free standing GaN. *Physica Status Solidi A*, **2004**, 201, 2782-2785		1
64	Reflection and absorption spectra of β-FeSi2 under pressure. *Thin Solid Films*, **2004**, 461, 171-173	2.2	2
63	Epitaxial growth of semiconducting β-FeSi2 and its application to light-emitting diodes. *Thin Solid Films*, **2004**, 461, 209-218	2.2	39
62	Epitaxial Growth of Semiconducting BaSi2Films on Si(111) Substrates by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2004**, 43, L478-L481	1.4	125
61	Epitaxial Growth of Semiconducting BaSi2Thin Films on Si(111) Substrates by Reactive Deposition Epitaxy. *Japanese Journal of Applied Physics*, **2004**, 43, 4155-4156	1.4	88
60	Conduction type and defect levels of β-FeSi2 films grown by MBE with different Si/Fe ratios. *Materials Science in Semiconductor Processing*, **2003**, 6, 307-309	4.3	5

59	Room-temperature ferromagnetism in Cr-doped GaN films grown by MOMBE on GaAs(111)A substrates. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2860-2863		13
58	Influence of boron-doped Si cap layer on the photoluminescence of β-FeSi2 particles embedded in Si matrix. *Journal of Applied Physics*, **2003**, 94, 1518-1520	2.5	11
57	Growth parameter dependence of HVPE GaN and polarity and crystal quality of the grown layers. *Journal of Crystal Growth*, **2002**, 237-239, 1089-1093	1.6	7
56	Investigation of direct and indirect band gaps of [100]-oriented nearly strain-free β-FeSi2 films grown by molecular-beam epitaxy. *Applied Physics Letters*, **2002**, 80, 556-558	3.4	28
55	Optical properties of βeSi2 under pressure. *Physical Review B*, **2002**, 65,	3.3	24
54	COMPARISON OF DONOR AND ACCEPTOR LEVELS IN UNDOPED, HIGH QUALITY β-FeSi2 FILMS GROWN BY MBE AND MULTI-LAYER METHOD. *International Journal of Modern Physics B*, **2002**, 16, 4314-4317	1.1	9
53	??????????β-FeSi2????????. *Materia Japan*, **2002**, 41, 342-347	0.1	
52	Investigation of the energy band structure of orthorhombic BaSi2 by optical and electrical measurements and theoretical calculations. *Applied Physics Letters*, **2002**, 81, 1032-1034	3.4	110
51	Dependence of photoluminescence from β-FeSi2 and induced deep levels in Si on the size of β-FeSi2 balls embedded in Si crystals. *Thin Solid Films*, **2001**, 381, 209-213	2.2	27
50	Optical Absorption Spectra of β-FeSi2 under Pressure. *Physica Status Solidi (B): Basic Research*, **2001**, 223, 259-263	1.3	3
49	Direct Growth of [100]-Oriented High-Quality β-FeSi2 Films on Si(001) Substrates by Molecular Beam Epitaxy. *Japanese Journal of Applied Physics*, **2001**, 40, L1008-L1011	1.4	43
48	Donor and Acceptor Levels in Undoped β-FeSi2 Films Grown on Si (001) Substrates. *Japanese Journal of Applied Physics*, **2001**, 40, L249-L251	1.4	19
47	Influence of Si growth temperature for embedding β-FeSi2 and resultant strain in β-FeSi2 on light emission from p-Si/β-FeSi2 particles/n-Si light-emitting diodes. *Applied Physics Letters*, **2001**, 79, 1804-1806	3.4	70
46	Structure Analysis of FeSi2 Embeded in Si by Transmission Electron Microscopy;. *Materia Japan*, **2001**, 40, 1013-1013	0.1	
45	Polarity of Hexagonal GaN Grown on GaAs (111)A and (111)B Surfaces by HVPE and Movpe. *Materials Research Society Symposia Proceedings*, **2000**, 639, 1181		1
44	Optimum thermal-cleaning condition of GaAs surface with a superior arsenic source: trisdimethylamino-arsine. *Journal of Crystal Growth*, **2000**, 209, 267-271	1.6	1
43	CBE growth of GaN on GaAs(001) and (111)B substrates using monomethylhydrazine. *Journal of Crystal Growth*, **2000**, 209, 373-377	1.6	3
42	Optimum annealing condition for 1.5μm photoluminescence from β-FeSi2 balls grown by reactive deposition epitaxy and embedded in Si crystal. *Journal of Luminescence*, **2000**, 87-89, 528-531	3.8	28

41	Growth of Mn doped epitaxial □FeSi2 films on Si(001) substrates by reactive deposition epitaxy. *Thin Solid Films*, **2000**, 369, 253-256	2.2	12
40	Superiority of an AlN Intermediate Layer for Heteroepitaxy of Hexagonal GaN. *Japanese Journal of Applied Physics*, **2000**, 39, 4869-4874	1.4	6
39	Room Temperature 1.6 □m Electroluminescence from a Si-Based Light Emitting Diode with □FeSi2 Active Region. *Japanese Journal of Applied Physics*, **2000**, 39, L1013-L1015	1.4	171
38	Control of the Conduction Type of Nondoped High Mobility □FeSi2 Films Grown from Si/Fe Multilayers by Change of Si/Fe Ratios. *Japanese Journal of Applied Physics*, **2000**, 39, L789-L791	1.4	36
37	Improvement of the Electrical Properties of □FeSi 2 Films on Si (001) by High-Temperature Annealing. *Japanese Journal of Applied Physics*, **2000**, 39, L233-L236	1.4	25
36	Ecologically Friendly Metal-Silicide Semiconductor Reserch. Fabrication of .BETA.-FeSi2 Spheres Embedded in Si by Molecular Beam Epitaxy and Enhancement of the Infrared Photoluminescence by High Temperature Annealing.. *The Review of Laser Engineering*, **2000**, 28, 99-102	0	
35	Growth of Continuous and Highly (100)-Oriented □FeSi 2 Films on Si(001) from Si/Fe Multilayers with SiO 2 Capping and Templates. *Japanese Journal of Applied Physics*, **1999**, 38, L878-L881	1.4	29
34	Growth of thick and pure cubic GaN on (001) GaAs by halide VPE. *Journal of Crystal Growth*, **1999**, 198-199, 1056-1060	1.6	13
33	Thick GaN Growth on GaAs(111) Substratres at 1000 □C with HVPE. *Physica Status Solidi A*, **1999**, 176, 421-424		3
32	Thick and Smooth Hexagonal GaN Growth on GaAs (111) Substrates at 1000□C with Halide Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1999**, 38, L700-L702	1.4	23
31	Improvement of 1.5 □m Photoluminescence from Reactive Deposition Epitaxy (RDE) Grown □FeSi 2 Balls in Si by High Temperature Annealing. *Japanese Journal of Applied Physics*, **1999**, 38, L620-L622	1.4	22
30	Dependence of GaN MOMBE growth on nitrogen source: ECR plasma gun structure and monomethyl-hydrazine. *Journal of Crystal Growth*, **1998**, 189-190, 380-384	1.6	3
29	Comparison between monomethyl hydrazine and ECR plasma activated nitrogen as a nitrogen source for CBE growth of GaN. *Journal of Crystal Growth*, **1998**, 188, 81-85	1.6	3
28	Growth condition dependence of GaN crystal structure on (0 0 1)GaAs by hydride vapor-phase epitaxy. *Journal of Crystal Growth*, **1998**, 189-190, 395-400	1.6	20
27	Fabrication of p-Si/□FeSi2 balls/n-si structures by MBE and their electrical and optical properties. *Journal of Luminescence*, **1998**, 80, 473-477	3.8	19
26	Photoluminescence from Reactive Deposition Epitaxy (RDE) Grown □FeSi 2 Balls Embedded in Si Crystals. *Japanese Journal of Applied Physics*, **1998**, 37, L1513-L1516	1.4	15
25	Magnetotransport Properties of a Single-Crystalline □FeSi 2 Layer Grown on Si(001) Substrate by Reactive Deposition Epitaxy. *Japanese Journal of Applied Physics*, **1998**, 37, L333-L335	1.4	3
24	Influence of As Autodoping from GaAs Substrates on Thick Cubic GaN Growth by Halide Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1998**, 37, L568-L570	1.4	11

23	Si Molecular Beam Epitaxial Growth over an Atomic-Layer Boron Adsorbed Si(001) Substrate and Its Electrical Properties. *Japanese Journal of Applied Physics*, **1997**, 36, 7146-7151	1.4	
22	Aggregation of Monocrystalline □FeSi 2 by Annealing and by Si Overlayer Growth. *Japanese Journal of Applied Physics*, **1997**, 36, L1225-L1228	1.4	45
21	Cubic Dominant GaN Growth on (001) GaAs Substrates by Hydride Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1997**, 36, L1-L3	1.4	52
20	Formation of □FeSi2Layers on Si(001) Substrates. *Japanese Journal of Applied Physics*, **1997**, 36, 3620-3624	1.4	84
19	Reactive deposition epitaxial growth of □FeSi2 layers on Si(001). *Applied Surface Science*, **1997**, 117-118, 303-307	6.7	32
18	Transfer efficiency of hot electrons in a metal(CoSi2)/insulator(CaF2) quantum interference transistor. *Surface Science*, **1996**, 361-362, 209-212	1.8	
17	Room-temperature observation of multiple negative differential resistance in a metal (CoSi2)/insulator (CaF2) quantum interference transistor structure. *Physica B: Condensed Matter*, **1996**, 227, 213-215	2.8	4
16	Epitaxial growth of a metal(CoSi2)/insulator(CaF2) nanometer-thick heterostructure and its application to quantum-effect devices. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **1995**, 13, 623-628	2.9	6
15	Metal (CoSi$_{bf 2}$)/Insulator (CaF$_{bf 2}$) Hot Electron Transistor Fabricated by Electron-Beam Lithography on a Si Substrate. *Japanese Journal of Applied Physics*, **1995**, 34, L1254-L1256	1.4	6
14	Multiple Negative Differential Resistance due to Quantum Interference of Hot Electron Waves in Metal (CoSi2)/Insulator (CaF2) Heterostructures and Influence of Parasitic Circuit Elements. *Japanese Journal of Applied Physics*, **1995**, 34, 4481-4484	1.4	4
13	Theoretical and measured characteristics of metal (CoSi/sub 2/)-insulator(CaF/sub 2/) resonant tunneling transistors and the influence of parasitic elements. *IEEE Transactions on Electron Devices*, **1995**, 42, 2203-2210	2.9	9
12	Quantum Interference of Electron Wave in Metal $bf (CoSi_{2})/Insulator (CaF_{2})$ Resonant Tunneling Hot Electron Transistor Structure. *Japanese Journal of Applied Physics*, **1994**, 33, L1762-L1765	1.4	10
11	Metal(CoSi2)/Insulator(CaF2) Resonant Tunneling Diode. *Japanese Journal of Applied Physics*, **1994**, 33, 57-65	1.4	32
10	Negative differential resistance of metal (CoSi2)/insulator (CaF2) triple-barrier resonant tunneling diode. *Applied Physics Letters*, **1993**, 62, 300-302	3.4	54
9	Room temperature negative differential resistance of metal (CoSi2)/insulator (CaF2) resonant tunnelling diode. *Electronics Letters*, **1992**, 28, 1432	1.1	18
8	Transistor action of metal (CoSi2)/insulator (CaF2) hot electron transistor structure. *Electronics Letters*, **1992**, 28, 1002-1004	1.1	21
7	Epitaxial growth and electrical conductance of metal(CoSi2)/insulator(CaF2) nanometer-thick layered structures on Si (111). *Journal of Electronic Materials*, **1992**, 21, 783-789	1.9	10
6	Negative differential resistance in metal (CoSi/sub 2/)/insulator (CaF/sub 2/) resonant tunneling diode. *IEEE Transactions on Electron Devices*, **1992**, 39, 2644	2.9	

5	Improvement of Organometallic Vapor Phase Epitaxy Regrown GaInAs/InP Heterointerface by Surface Treatment. *Japanese Journal of Applied Physics*, **1991**, 30, L1702-L1704	1.4	4
4	Improvement of Regrown Interface in InP Organo-Metallic Vapor Phase Epitaxy. *Japanese Journal of Applied Physics*, **1991**, 30, L672-L674	1.4	11
3	Solid-Phase Crystallization of GeSn Thin Films on GeO2-Coated Glass. *Physica Status Solidi - Rapid Research Letters*,2100509	2.5	0
2	Ferrimagnetic□ferromagnetic phase transition in Mn4N films favored by non-magnetic In doping. *Journal Physics D: Applied Physics*,	3	4
1	Recent Progress Toward Realization of High-Efficiency BaSi2 Solar Cells: Thin-Film Deposition Techniques and Passivation of Defects. *Physica Status Solidi (A) Applications and Materials Science*,2100593	1.6	4